

Rev. V1

### **Features**

Saturated Power: 75 WDrain Efficiency: 70%Small Signal Gain: 20 dB

Lead-Free Air Cavity Ceramic Package

RoHS\* Compliant

### **Applications**

- UHF Radar
- Public Safety Radio
- ISM
- General Amplification

### **Description**

The MAPL-100405-060C is an LDMOS Transistor suitable for use in power amplifier applications in the DC to 1 GHz frequency band. Features include high gain and a thermally-enhanced package. Manufactured with MACOM's advanced LDMOS process, this device provides excellent thermal performance and superior reliability.

Offered in a thermally-enhanced flange package, the MAPL-100405-060C provides superior performance under CW operation allowing customers to improve SWaP-C benchmarks in their next generation systems.

# **Typical RF Performance:**

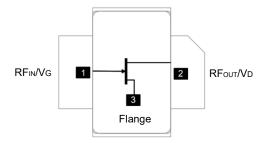
• Pulse width of 15msec and 25% duty,  $P_{IN}$  = 25 dBm,  $V_{DS}$  = 50 V,  $I_{DQ}$  = 100 mA,  $T_C$  = 25°C

Frequency (GHz)	Output Power (dBm)	Gain (dB)	η <sub>□</sub> (%)
0.420	48.1	23.1	60.2
0.435	48.5	23.5	70.3
0.450	48.0	23.0	61.7



440206

### **Functional Schematic**



# **Pin Configuration**

Pin#	Pin Name	Function
1	RF <sub>IN</sub> / V <sub>G</sub>	RF Input / Gate
2	RF <sub>OUT</sub> / V <sub>D</sub>	RF Output / Drain
3	Flange <sup>1</sup>	Ground / Source

<sup>1.</sup> The flange on the package bottom must be connected to RF,  $\ensuremath{\mathsf{DC}}$  and thermal ground.

## **Ordering Information**

Part Number	MOQ Increment		
MAPL-100405-060C00	Bulk		
MAPL-100405-060SB1	Sample Board		

<sup>\*</sup> Restrictions on Hazardous Substances, compliant to current RoHS EU directive.



Rev. V1

# RF Electrical Specifications<sup>1</sup>:

Freq. = 435 MHz, CW,  $P_{IN}$  = 25 dBm,  $T_A$  = +25C,  $V_{DS}$  = 50 V,  $I_{DQ}$  = 100 mA

Parameter	Units	Min.	Тур.	Max.
Output Power	W	70.0	73.5	_
Drain Efficiency	%	68.0	69.7	_
Power Gain	dB	23.4	23.7	_

<sup>1.</sup> Final testing and screening for all transistor sales is performed using the MAPL-100405-060SB1 at 435 MHz.

# **Absolute Maximum Ratings<sup>2,3</sup>**

Parameter	Absolute Maximum		
Drain-Source Voltage	105 V		
Gate Voltage	-6 +12 V		
Operating Voltage	0 to + 55 V		
Mounting Temperature	245°C		
Junction Temperature⁴	+225°C		
Operating Temperature	-40°C to +85°C		
Storage Temperature	-65C to +150°C		

- 2. Exceeding any one or combination of these limits may cause permanent damage to this device.
- MACOM does not recommend sustained operation near these survivability limits.
- 4. Junction Temperature  $(T_J) = T_C + \Theta jc * (V * I)$

Typical thermal resistance (Θjc) = 1.63 °C/W for CW.

a) For 
$$T_C = +25^{\circ}C$$
,

b) For  $T_C = +85^{\circ}C$ ,

T<sub>J</sub> = 166°C @ P<sub>DISS</sub>= 50 W

# **Handling Procedures**

Please observe the following precautions to avoid damage:

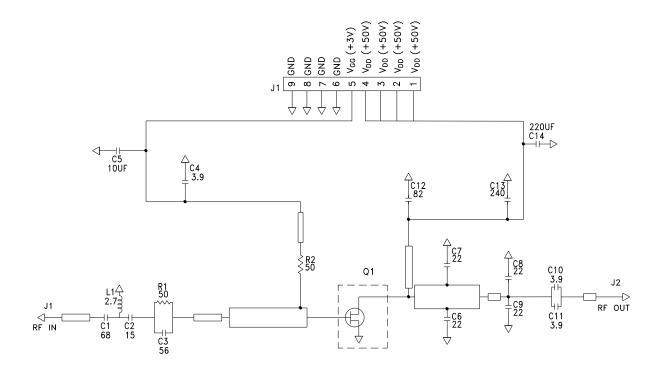
### **Static Sensitivity**

These electronic devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.



Rev. V1

# Evaluation Test Fixture and Recommended Tuning Solution, 420 - 450 MHz



### **Description**

Parts measured on evaluation board (50-mil thick RO3006). Matching is provided using a combination of lumped elements and transmission lines as shown in the simplified schematic above. Recommended tuning solution component placement, transmission lines, and details are shown on the next page.

### **Biasing Sequence**

#### **Bias ON**

- 1. Ensure RF is turned off
- 2. Apply nominal drain voltage
- 3. Bias gate to desired quiescent drain current
- 4. Apply RF

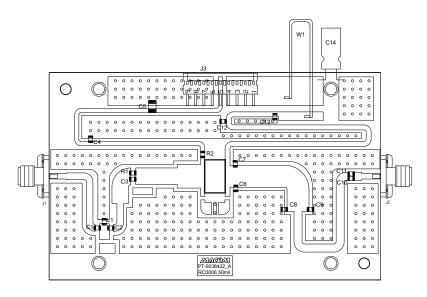
#### **Bias OFF**

- 1. Turn RF off
- 2. Turn-off drain voltage
- 3. Turn-off gate voltage



Rev. V1

# Evaluation Test Fixture and Recommended Tuning Solution, 420 - 450 MHz



# **Assembly Parts List**

Reference Designator	Description	Qty.
C1	CAP, 68 pF, +/-0.1pF, 250V, 0805, ATC600F	1
C2	CAP, 15 pF, +/-0.1pF, 250V, 0805, ATC600F	1
C3	CAP, 56 pF +/- 5%, 250V, 0805, ATC 600F	1
C4, C10, C11	CAP, 3.9 pF, +/-0.1pF, 250V, 0805, ATC600F	3
C5	10uF 1210in T10% 125C 100V	1
C6, C7, C8, C9	CAP, 22 pF +/- 5%, 250V, 0805, ATC 600F	4
C12	CAP, 82 pF +/- 5%, 250V, 0805, ATC 600F	1
C13	CAP, 240 pF +/- 5%, 250V, 0805, ATC 600F	1
C14	CAP, 220uF, 100V, Electrolytic	1
L1	2.7nH 0603	1
R1, R2	RES, 50 OHM, 0805	1
W1	18 +/- 2AWG 4.25" Wire	1
J1,J2	CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST	2
J3	HEADER RT>PLZ .1CEN LK 9POS	1
_	PCB, RO3006, Er = 6.15, h = 50 mil	1
Q1	MAPL-100405-060C	1

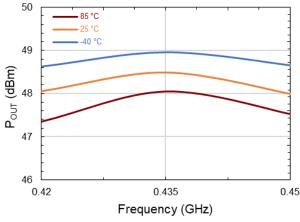


Rev. V1

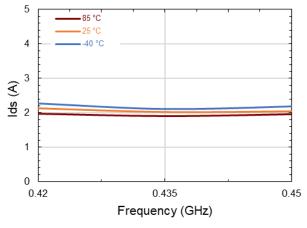
### Typical Performance Curves as Measured in the 420 – 450 MHz Evaluation Test Fixture

Pulsed 15 msec/25%, Pin = 25 dBm,  $V_{DS}$  = 50 V,  $I_{DQ}$  = 100 mA, Frequency = 435 MHz (Unless Otherwise Noted) For Engineering Evaluation Only – This data does not Modify MACOM's Datasheet Limits.

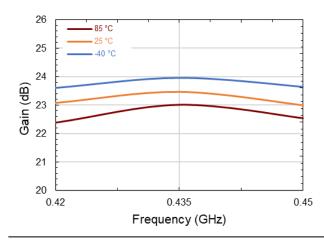
### Output Power vs. Temperature and Frequency



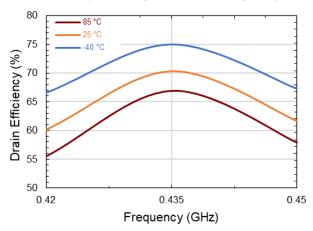
## Drain Current vs. Temperature and Frequency



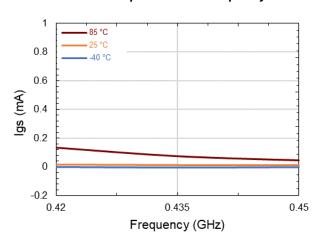
#### Large Signal Gain vs. Temperature and Frequency



### Drain Efficiency vs. Temperature and Frequency



### Gate Current vs. Temperature and Frequency



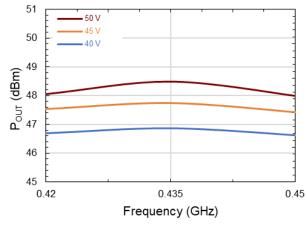


Rev. V1

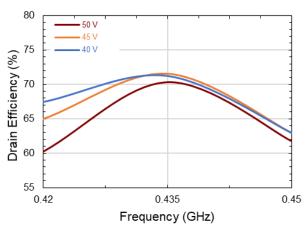
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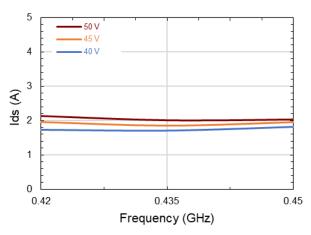
### Output Power vs. VDS and Frequency



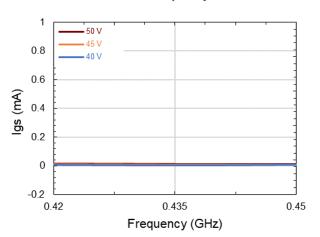
### Drain Efficiency vs. V<sub>DS</sub> and Frequency



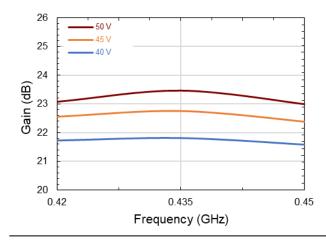
### Drain Current vs. VDS and Frequency



Gate Current vs. V<sub>DS</sub> and Frequency



### Large Signal Gain vs. VDS and Frequency



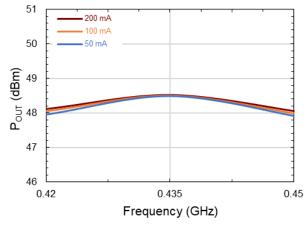


Rev. V1

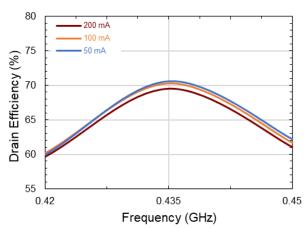
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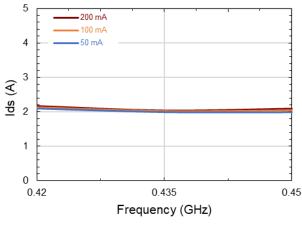
#### Output Power vs. Inc. and Frequency



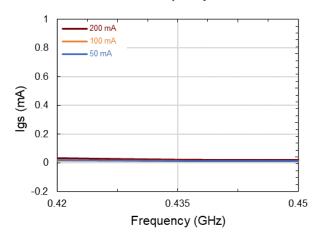
#### Drain Efficiency vs. Inc. and Frequency



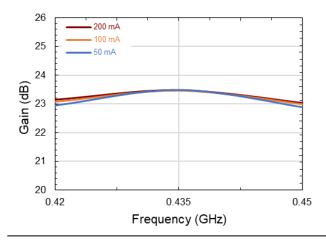
### Drain Current vs. IDQ and Frequency



Gate Current vs. IDQ and Frequency



#### Large Signal Gain vs. IDQ and Frequency



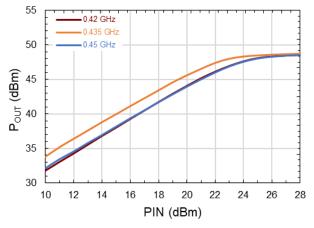


Rev. V1

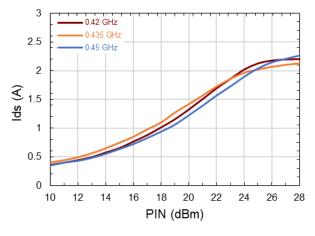
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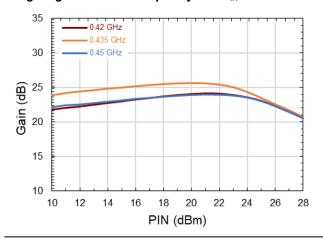
#### Output Power vs. Frequency and PIN



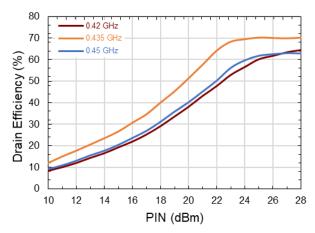
### Drain Current vs. Frequency and PIN



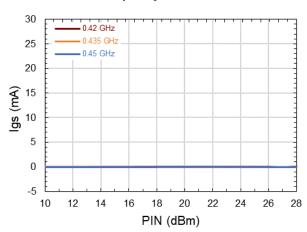
### Large Signal Gain vs. Frequency and PIN



#### Drain Efficiency vs. Frequency and PIN



### Gate Current vs. Frequency and PIN



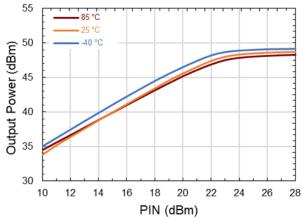


Rev. V1

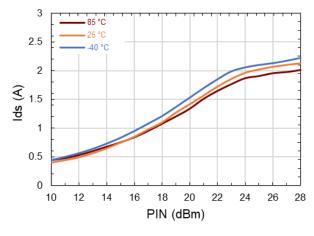
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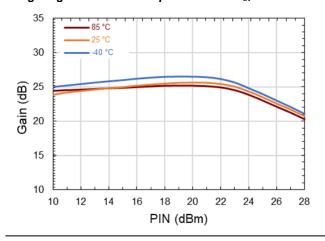
#### Output Power vs. Temperature and PIN



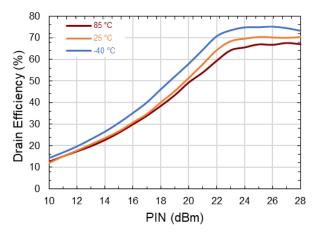
Drain Current vs. Temperature and PIN



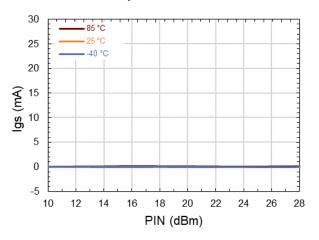
### Large Signal Gain vs. Temperature and PIN



#### Drain Efficiency vs. Temperature and PIN



### Gate Current vs. Temperature and PIN



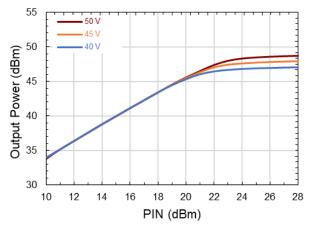


MAPL-100405-060C Rev. V1

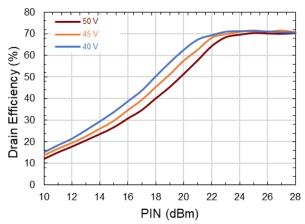
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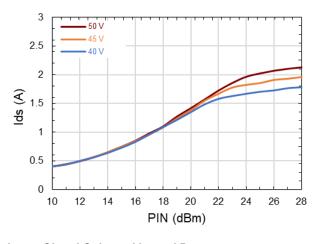
#### Output Power vs. Vns and Pin



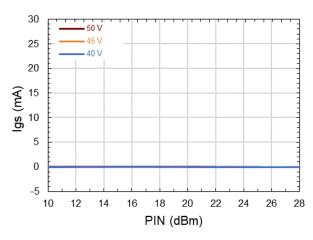
## Drain Efficiency vs. Vns and PIN



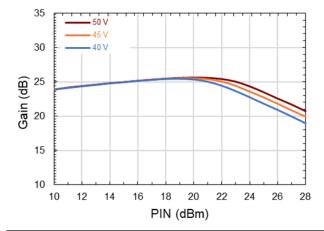
### Drain Current vs. V<sub>DS</sub> and P<sub>IN</sub>



Gate Current vs. VDS and PIN



### Large Signal Gain vs. VDS and PIN



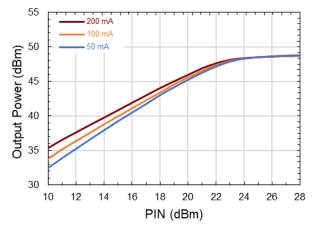


Rev. V1

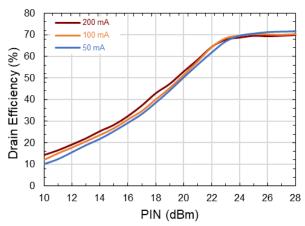
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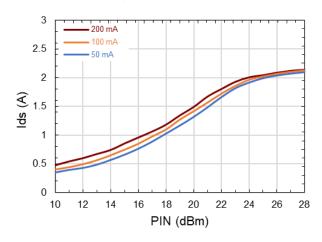
#### Output Power vs. Inc. and PIN



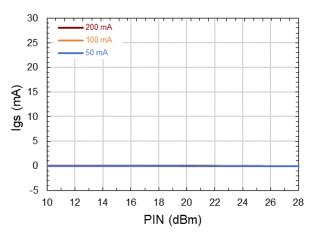
### Drain Efficiency vs. Inc and Pin



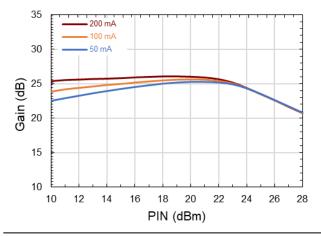
### Drain Current vs. IDQ and PIN



Gate Current vs. IDQ and PIN



### Large Signal Gain vs. IDQ and PIN





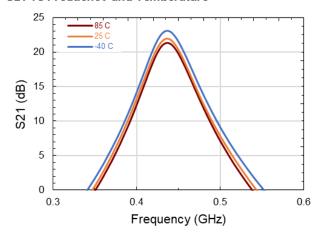
Rev. V1

# Typical Performance Curves as Measured in the 420 – 450 MHz Evaluation Test Fixture

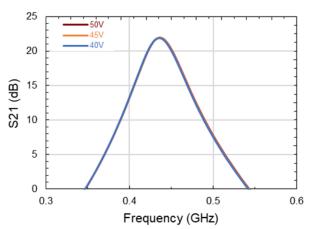
CW,  $V_{DS}$  = 50V,  $I_{DQ}$  = 100 mA, Pin=-20dBm

For Engineering Evaluation Only—This data does not Modify MACOM's Datasheet Limits.

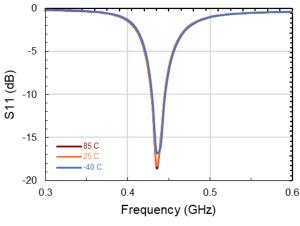
#### S21 vs Frequency and Temperature



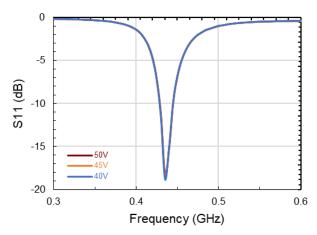
#### S21 vs Frequency and Vos



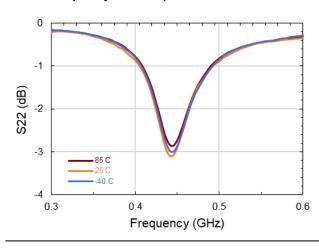
### S11 vs Frequency and Temperature



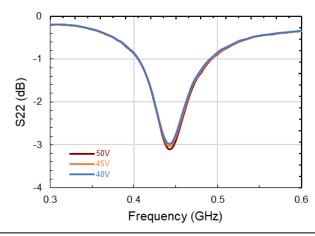
S11 vs Frequency and V<sub>DS</sub>



#### S22 vs Frequency and Temperature



S22 vs Frequency and V<sub>DS</sub>





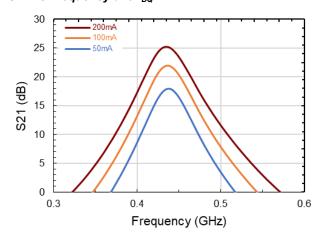
Rev. V1

# Typical Performance Curves as Measured in the 420 – 450 MHz Evaluation Test Fixture

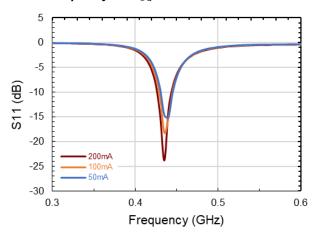
CW,  $V_{DS}$  = 50V,  $I_{DQ}$  = 100 mA, Pin=-20dBm

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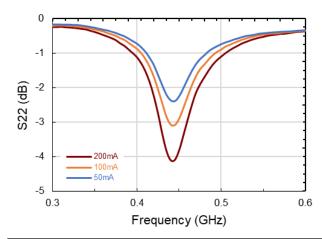
### S21 vs Frequency and IDQ



### S11 vs Frequency and IDQ



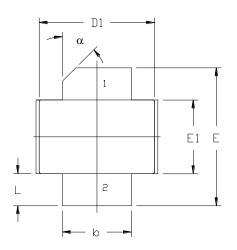
### S22 vs Frequency and IDQ

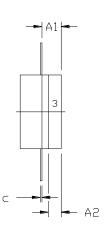


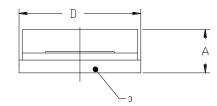


Rev. V1

# Lead-free 440206 Package Dimensions







#### NUTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M 1994.
- 2. CONTROLLING DIMENSION: INCH.
- 3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
- 4. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF 0.008' IN ANY DIRECTION.

	INCHES		MILLIMETERS		NOTES
DIM	MIN	MAX	MIN	MAX	
Α	0.125	0.145	3.18	3.68	
A1	0.057	0.067	1.45	1.70	
A2	0.035	0.045	0.89	1.14	
b	0.210	0.220	5.33	5.59	2×
С	0.004	0.006	0.10	0.15	2×
D	0.375	0.385	9.53	9.78	
D1	0.355	0.365	9.02	9.27	
Е	0.400	0.460	10.16	11.68	
E1	0.225	0.235	5.72	5.97	
L	0.085	0.115	2.16	2.92	2×
α	45° REF		45° REF		

PIN 1. DRAIN

- 2. GATE
- 3. SOURCE

# LDMOS Transistor, 75 W, 50 V DC - 1 GHz



MAPL-100405-060C

Rev. V1

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